



IGBT Discrete

V_{CE}	650	V
I_C	75	A
$V_{CE(SAT)}$ $I_C=75A$	1.65	V

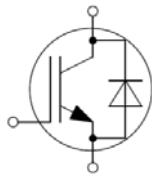
Applications

- High frequency switching application
- Resonant converters
- Uninterruptible power supply
- Welding converters

Features

- High speed smooth switching device for hard & soft switching
- Maximum junction temperature 175°C
- Positive temperature coefficient
- High ruggedness, temperature stable
- Pb-free lead plating; RoHS compliant

Circuit



Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	650	V
DC Collector Current, limited by T_{jmax} $T_C=25^\circ C$ value limited by bondwire $T_C=100^\circ C$	I_C	85 80	A
Diode Forward Current, limited by T_{jmax} $T_C=25^\circ C$ value limited by bondwire $T_C=100^\circ C$	I_F	85 80	A
Continuous Gate-Emitter Voltage	V_{GE}	± 20	V
Transient Gate-Emitter Voltage ($t_p \leq 10\mu s, D < 0.010$)	V_{GE}	± 30	V
Turn off Safe Operating Area $V_{CE} \leq 650V$, $T_j \leq 150^\circ C$		300	A
Pulsed Collector Current, $V_{GE}=15V$, t_p limited by T_{jmax}	I_{CM}	300	A
Diode Pulsed Current, t_p limited by T_{jmax}	I_{Fpuls}	300	A
Power Dissipation, $T_j=175^\circ C, T_C=25^\circ C$	P_{tot}	395	W
Operating Junction Temperature	T_j	-40...+175	$^\circ C$
Storage Temperature	T_s	-55...+150	$^\circ C$
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^\circ C$



■ Electrical Characteristics of the IGBT (T_j= 25°C unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV _{CES}	V _{GE} =0V, I _C =250μA	650		-	V
Gate Threshold Voltage	V _{GE(th)}	V _{GE} =V _{CE} , I _C =0.75mA	4.25	5.05	5.85	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V, I _C =75A T _j =25°C, T _j =125°C T _j =150°C	1.45	1.65 2.05 2.15	1.95	V
Zero Gate Voltage Collector Current	I _{CES}	V _{CE} =650V, V _{GE} =0V T _j = 25°C, T _j =150°C			0.25 3.00	mA
Gate-Emitter Leakage Current	I _{GES}	V _{CE} = 0V, V _{GE} = ± 20V			200	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Input Capacitance	C _{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	-	8.15	-	nF
Reverse Transfer Capacitance	C _{res}		-	0.24	-	
Gate Charge	Q _G	V _{CC} =300V, I _C =75A, V _{GE} =15V	-	0.58	-	uC



■ Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25°C						
Turn-on Delay Time	t _{d(on)}	V _{CC} =300V, I _C =75A, V _{GE} = 0V~15V, R _g =10Ω, L _s =60nH	-	75	-	ns
Rise Time	t _r		-	91	-	ns
Turn-on Energy	E _{on}		-	2.5	-	mJ
Turn-off Delay Time	t _{d(off)}		-	468	-	ns
Fall Time	t _f		-	41	-	ns
Turn-off Energy	E _{off}		-	1.3	-	mJ
Total switching energy	E _{ts}				3.8	
Dynamic , at T_j= 125°C						
Turn-on Delay Time	t _{d(on)}	V _{CC} =300V, I _C =75A, V _{GE} = 0V~15V, R _g =10Ω, L _s =60nH	-	70	-	ns
Rise Time	t _r		-	79	-	ns
Turn-on Energy	E _{on}		-	3.5	-	mJ
Turn-off Delay Time	t _{d(off)}		-	508	-	ns
Fall Time	t _f		-	48	-	ns
Turn-off Energy	E _{off}		-	1.6	-	mJ
Total switching energy	E _{ts}				5.1	
Dynamic , at T_j= 150°C						
Turn-on Delay Time	t _{d(on)}	V _{CC} =300V, I _C =75A, V _{GE} = 0V~15V, R _g =10Ω, L _s =60nH	-	68	-	ns
Rise Time	t _r		-	76	-	ns
Turn-on Energy	E _{on}		-	3.7	-	mJ
Turn-off Delay Time	t _{d(off)}		-	519	-	ns
Fall Time	t _f		-	52	-	ns
Turn-off Energy	E _{off}		-	1.7	-	mJ
Total switching energy	E _{ts}				5.4	

■ Electrical Characteristics of the Diode (T_j= 25°C unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Diode Forward Voltage	V _F	I _F = 75A T _j = 25°C, T _j = 125°C T _j = 150°C	1.30	1.61 1.45 1.41	1.90	V

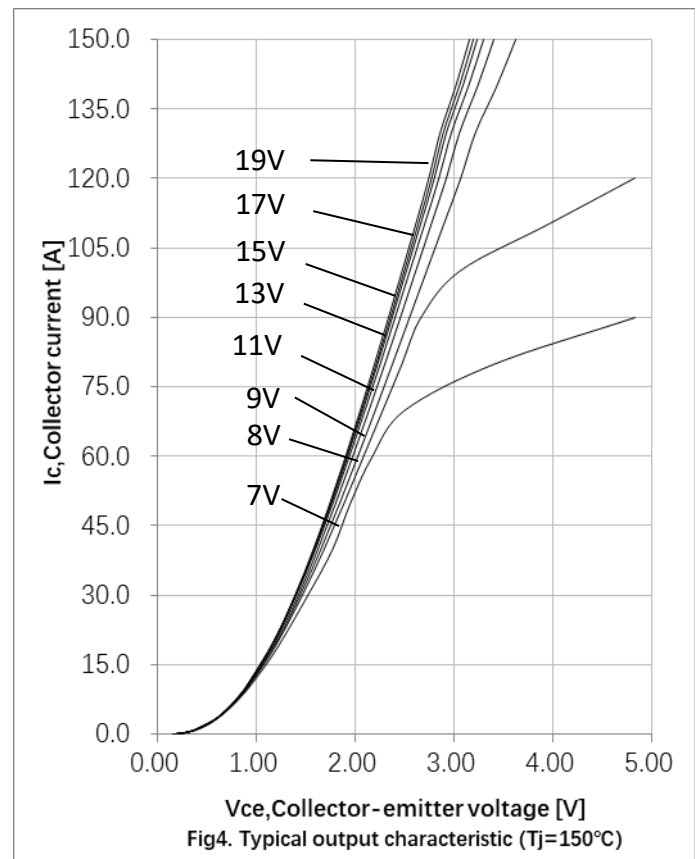
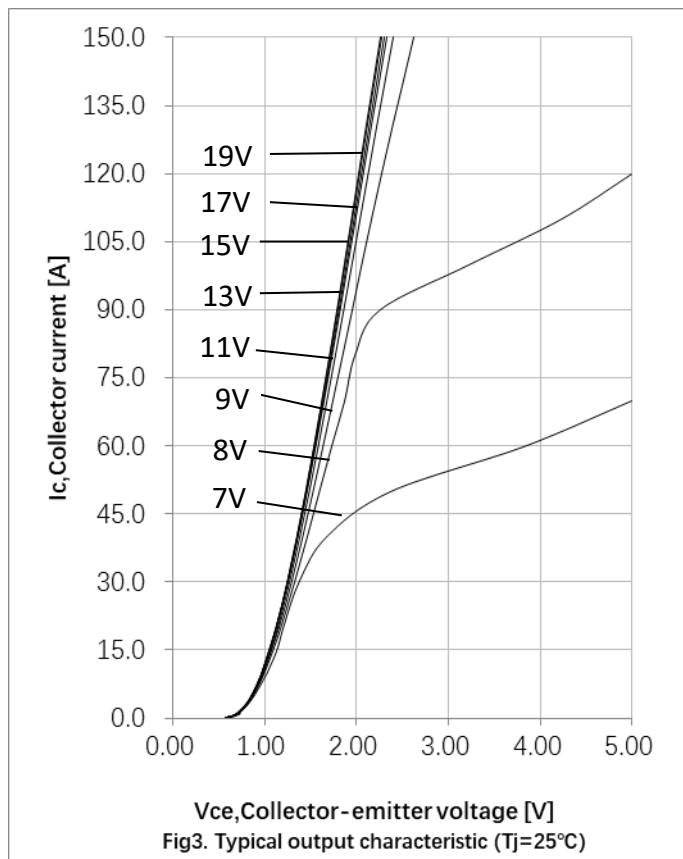
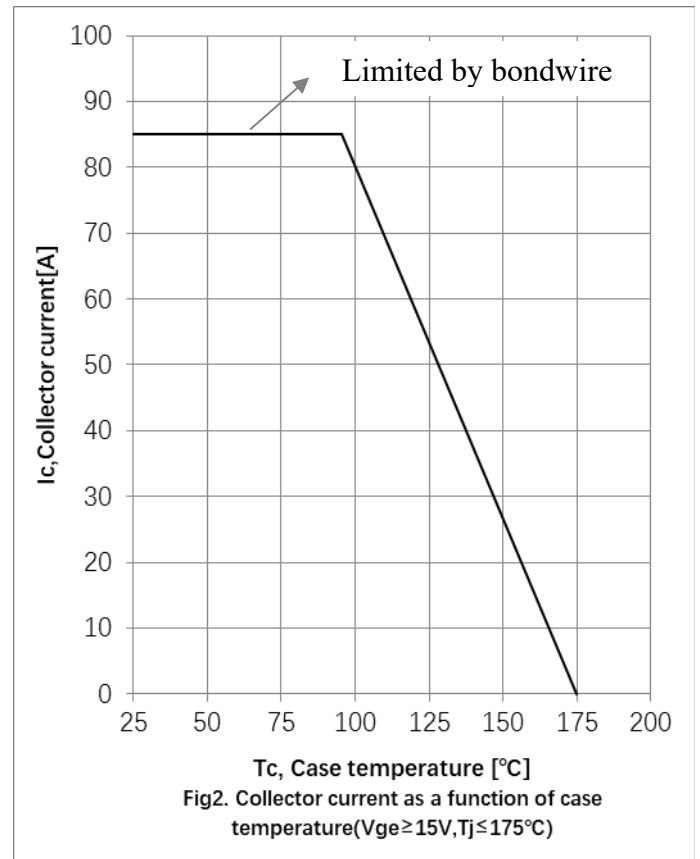
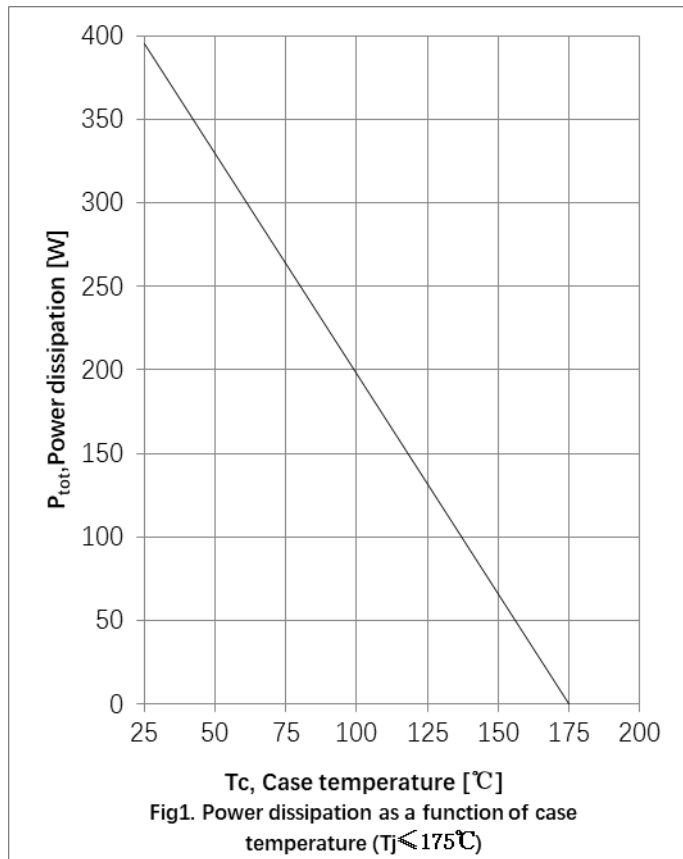


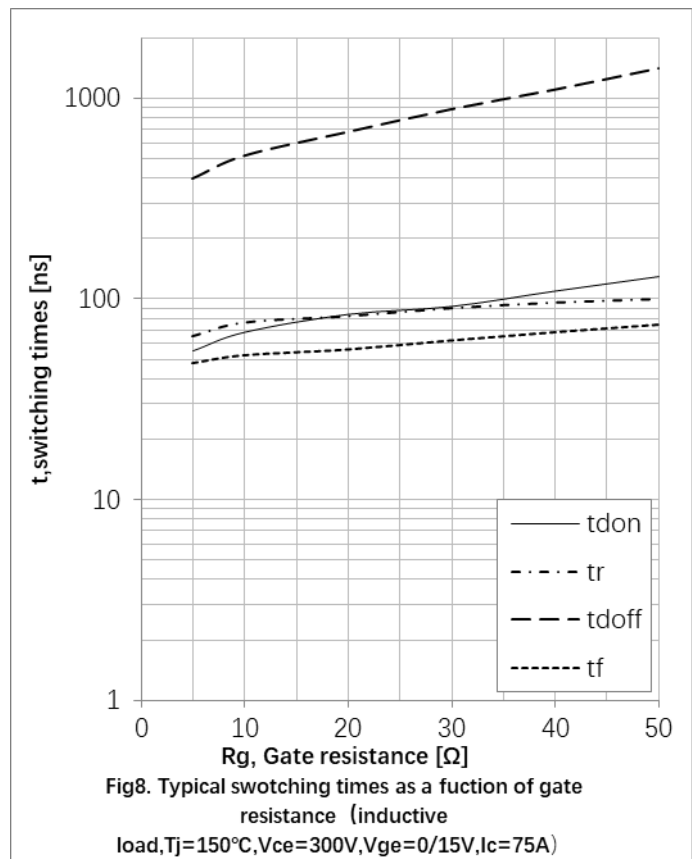
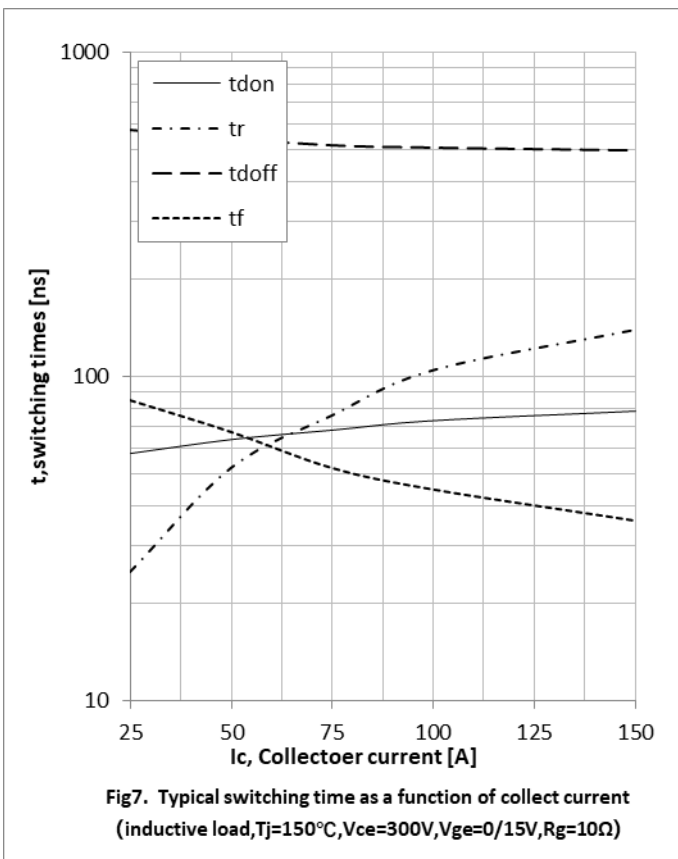
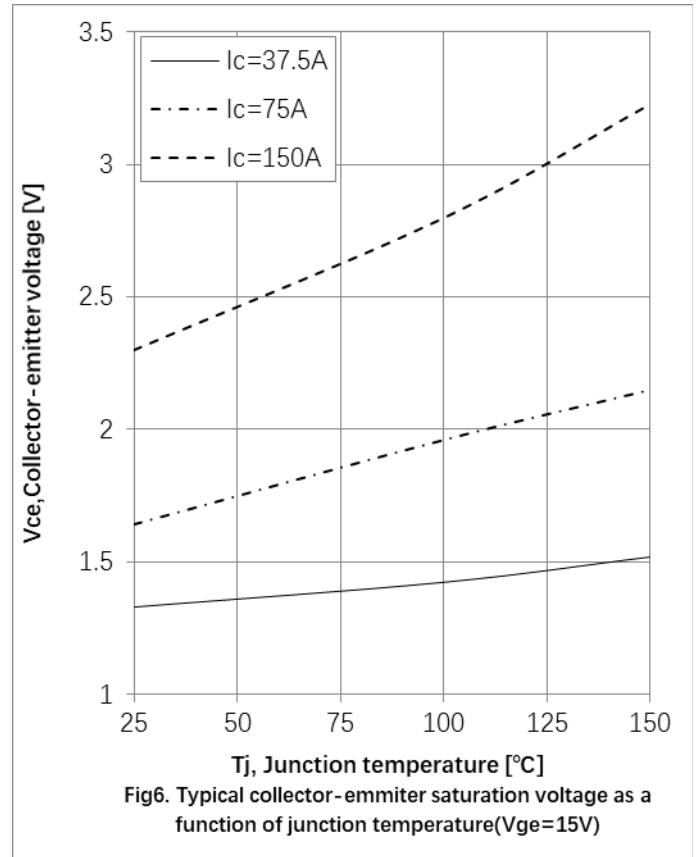
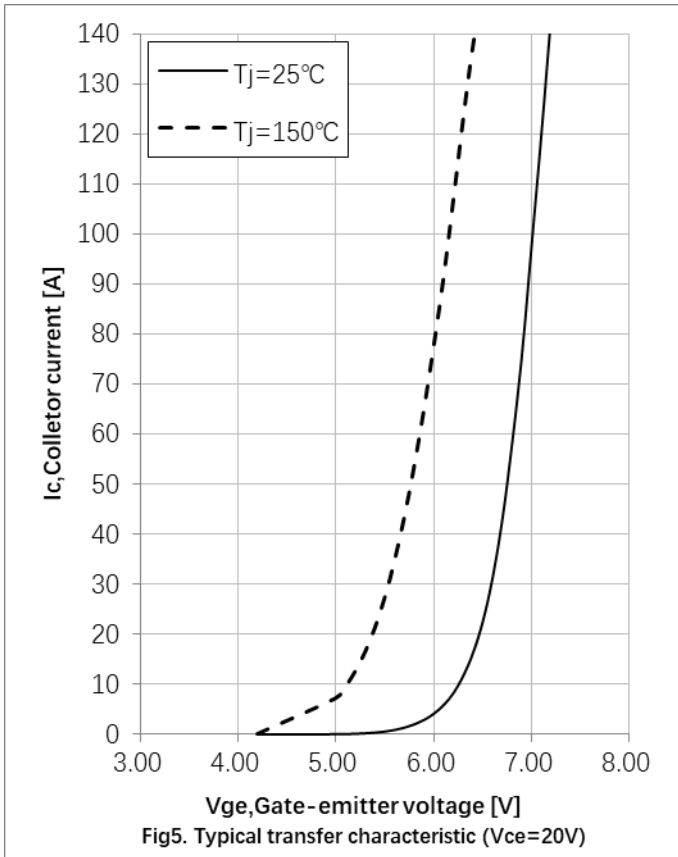
■ Electrical Characteristics of the Diode

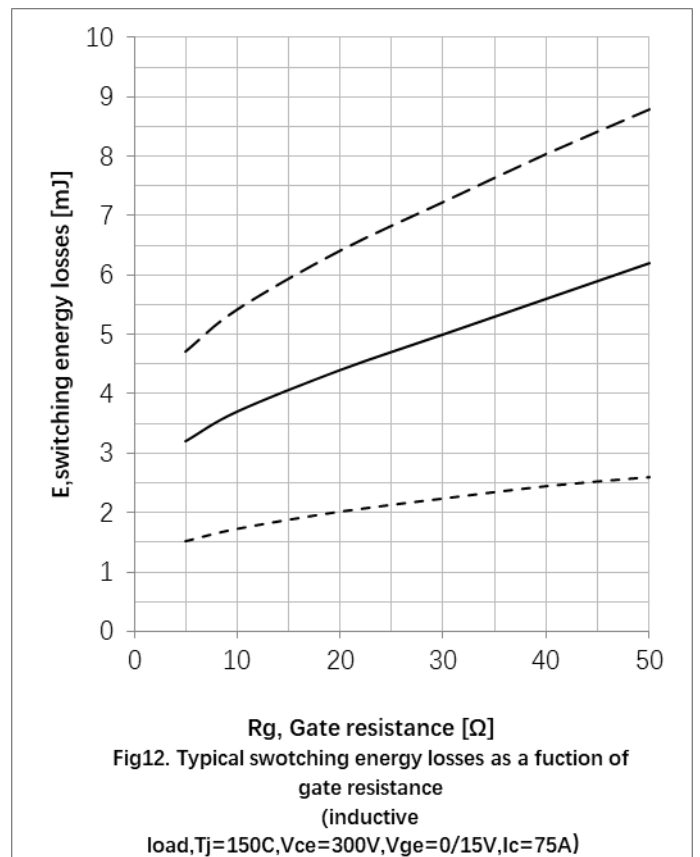
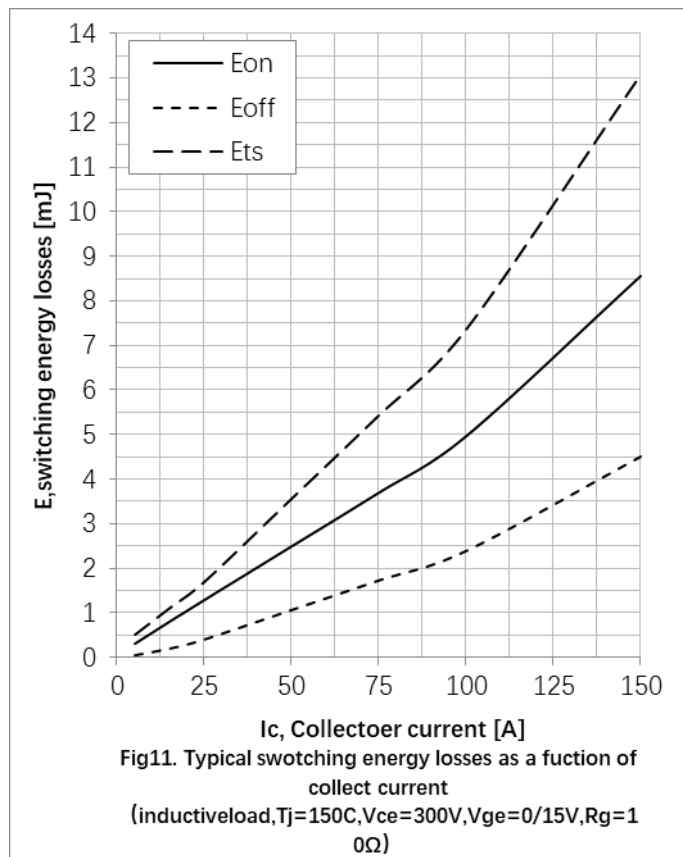
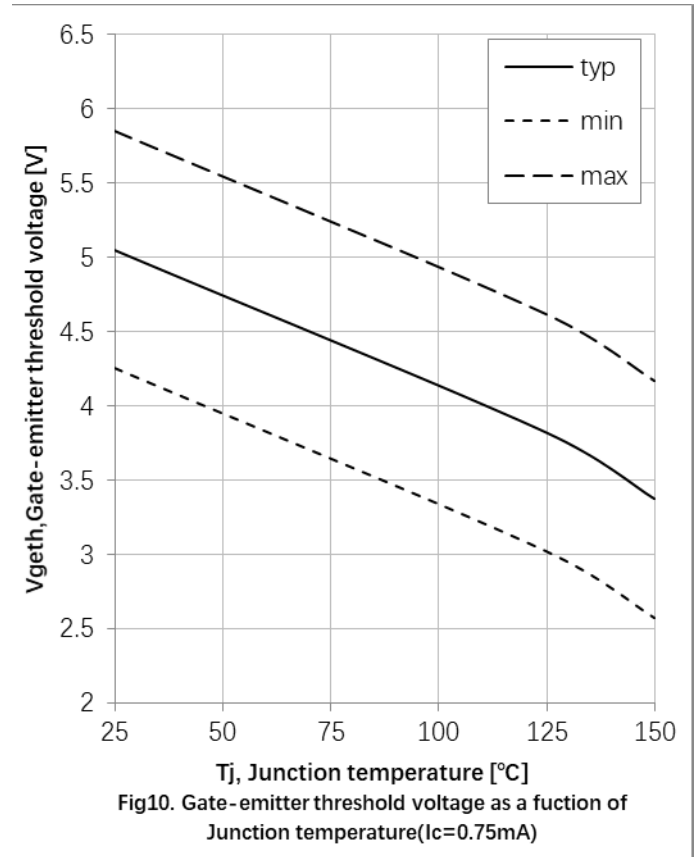
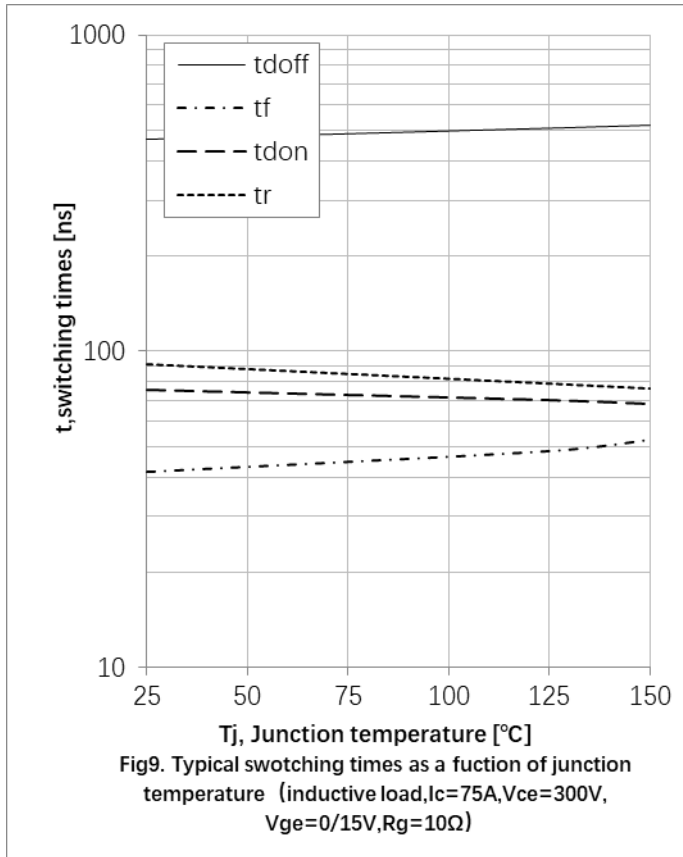
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25°C						
Reverse Recovery Current	I _{rr}	I _F =75A, V _R =300V -di/dt=550A/μs,	-	13	-	A
Reverse Recovery Charge	Q _{rr}		-	0.73	-	uC
Diode reverse recovery time	t _{rr}		-	100	-	ns
Reverse Recovery Energy	E _{rec}		-	0.12		mJ
Dynamic , at T_j= 125°C						
Reverse Recovery Current	I _{rr}	I _F =75A, V _R =300V -di/dt=550A/μs,	-	32	-	A
Reverse Recovery Charge	Q _{rr}		-	3.4	-	uC
Diode reverse recovery time	t _{rr}		-	140	-	ns
Reverse Recovery Energy	E _{rec}		-	0.4		mJ
Dynamic , at T_j= 150°C						
Reverse Recovery Current	I _{rr}	I _F =75A, V _R =300V -di/dt=550A/μs,	-	38	-	A
Reverse Recovery Charge	Q _{rr}		-	3.58	-	uC
Diode reverse recovery time	t _{rr}		-	160	-	ns
Reverse Recovery Energy	E _{rec}		-	0.49		mJ

■ Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	R _{th(j-c)}	0.38	K/W
Diode Thermal Resistance, Junction - Case	R _{th(j-c)}	0.45	K/W
Thermal Resistance, Junction - Ambient	R _{th(j-a)}	40	K/W







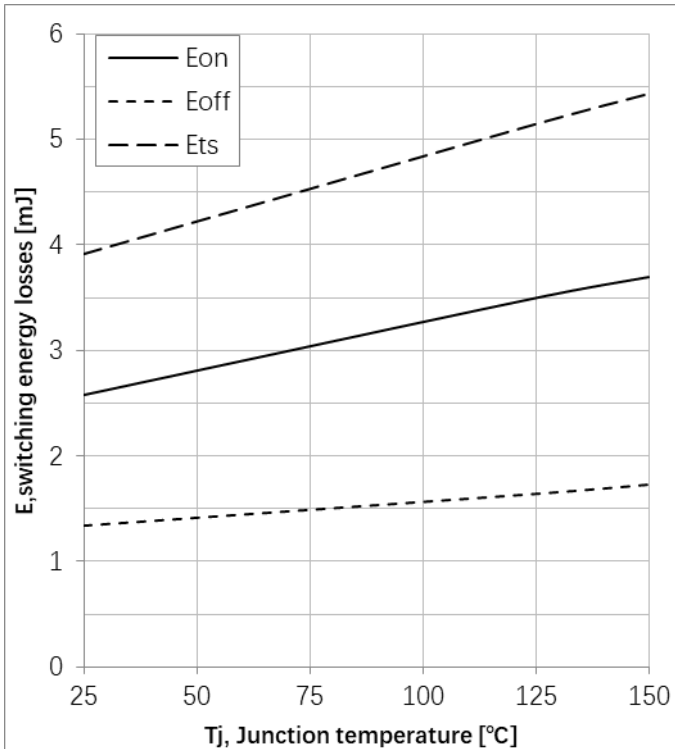


Fig13. Typical switching energy losses as a function of Junction temperature (inductive load, I_c=75A, V_{ce}=300V, V_{ge}=0/15V, R_g=10Ω)

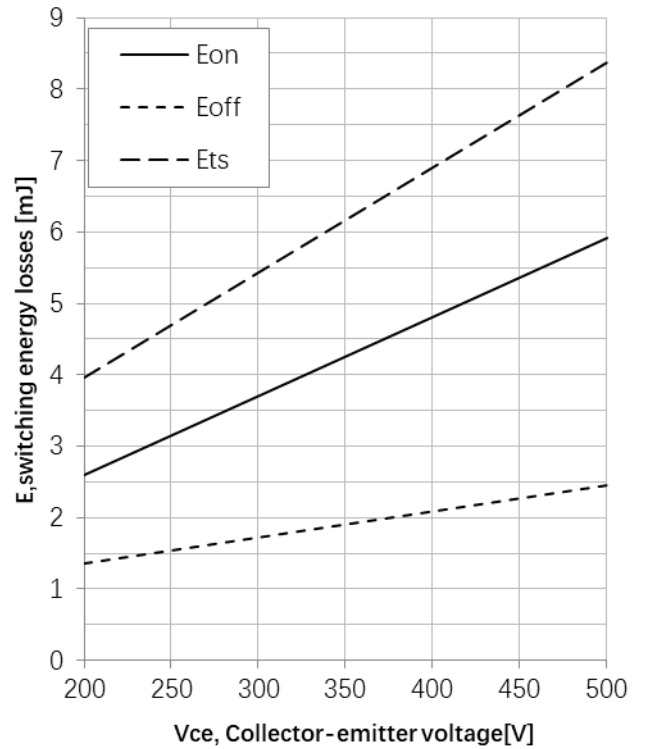


Fig14. Typical switching energy losses as a function of collector-emitter voltage (inductive load, T_j=150C, I_c=75A, V_{ge}=0/15V, R_g=10Ω)

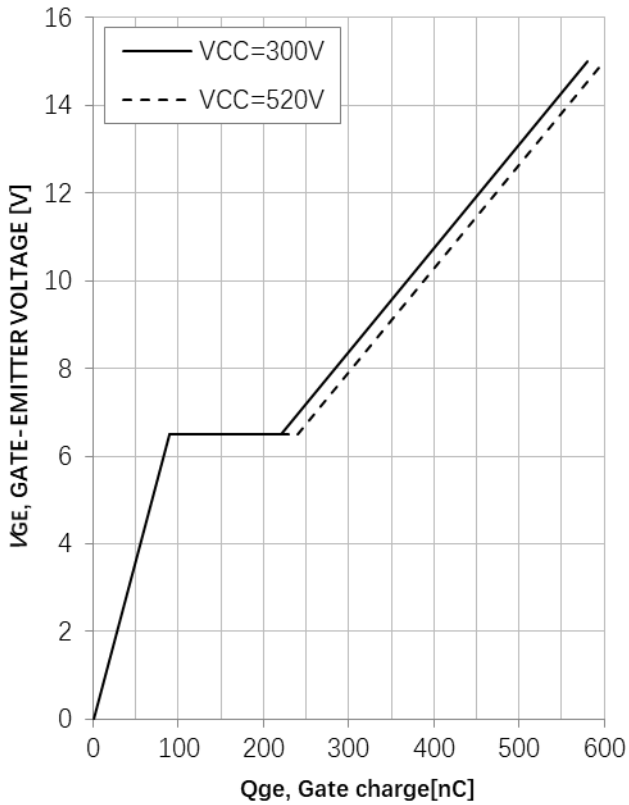


Fig15. Typical gate charge

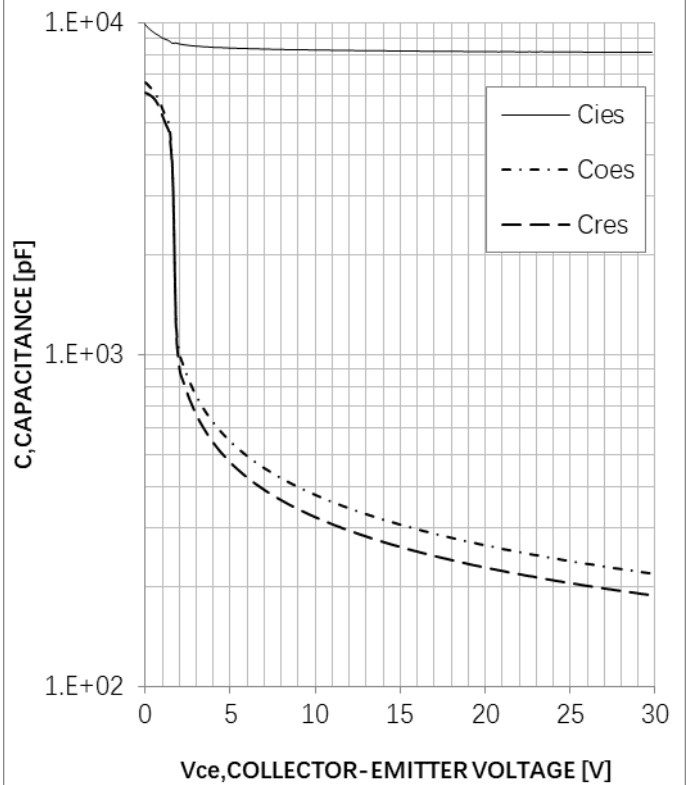
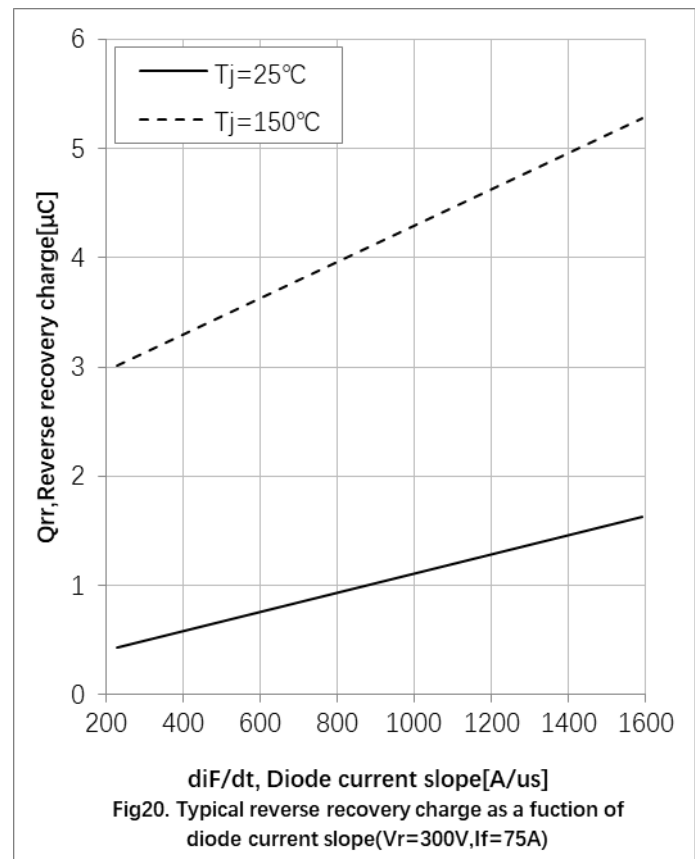
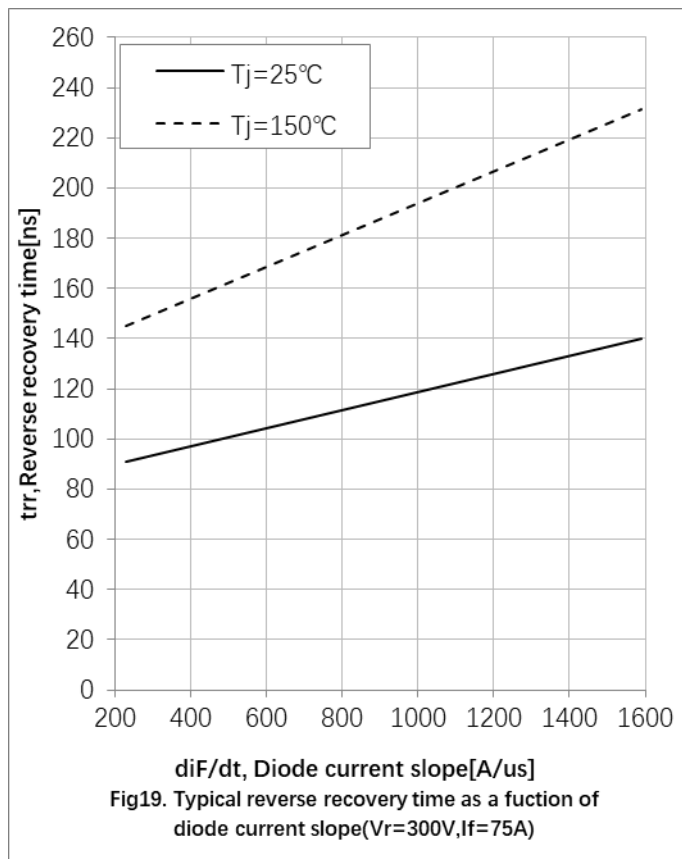
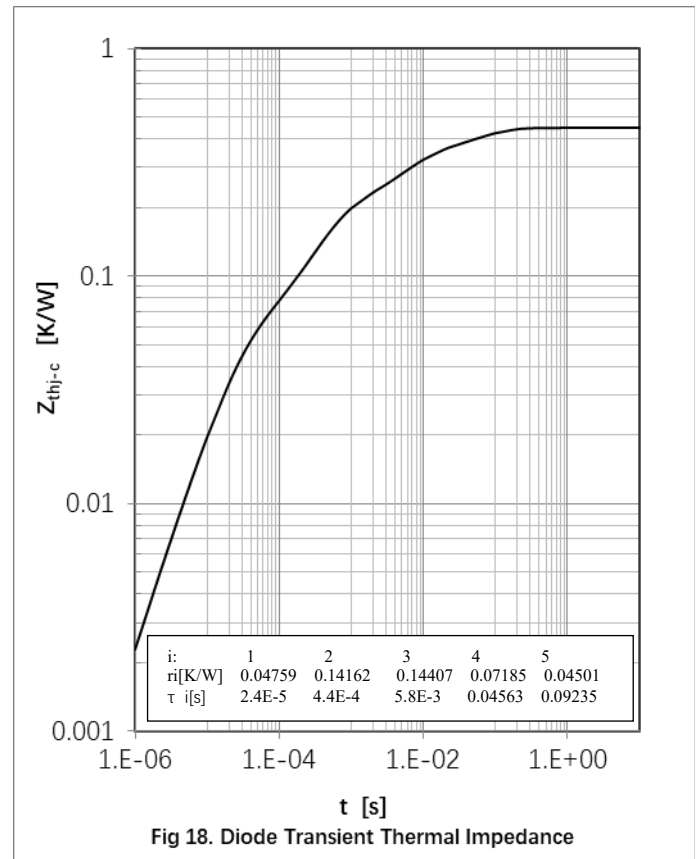
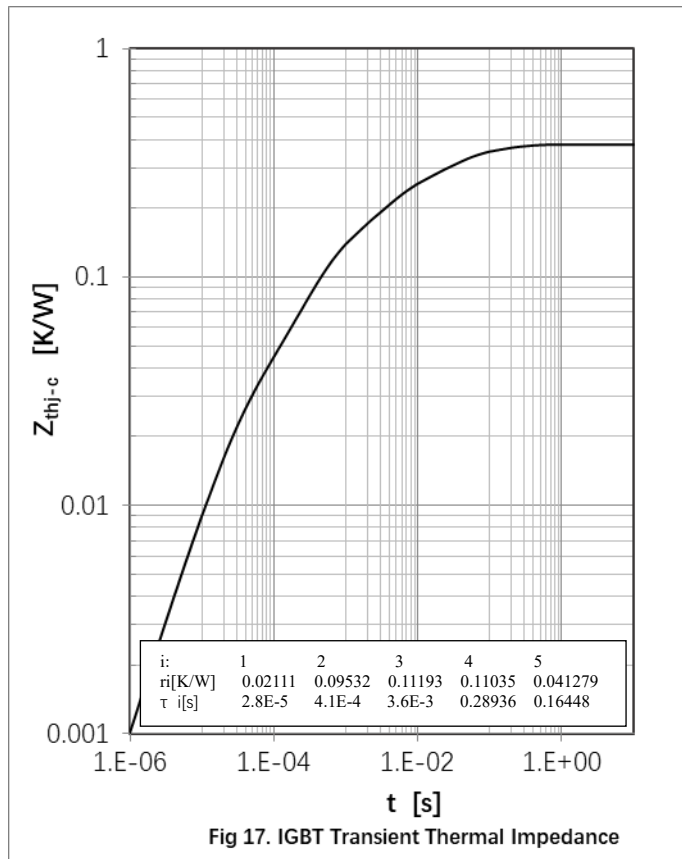
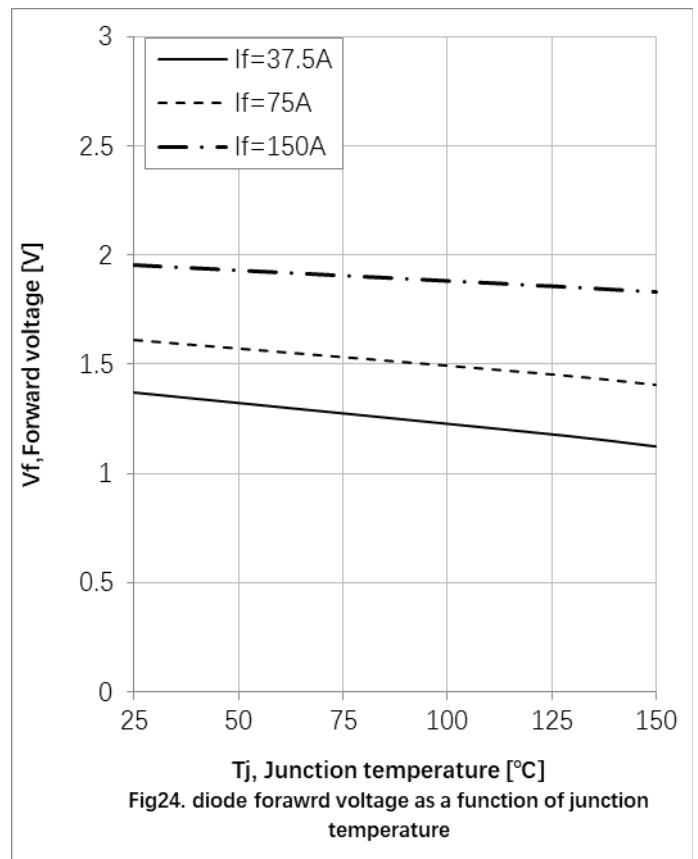
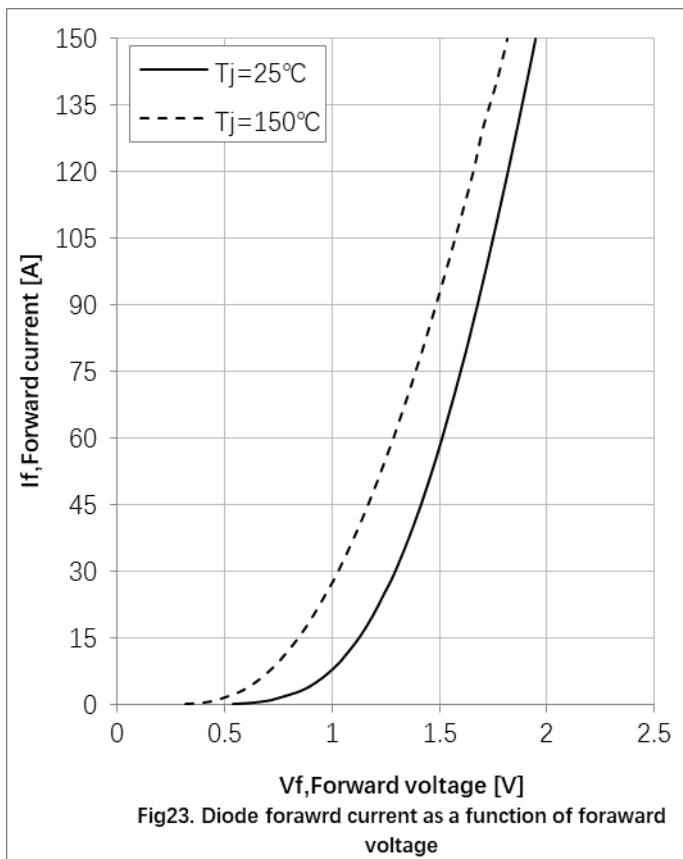
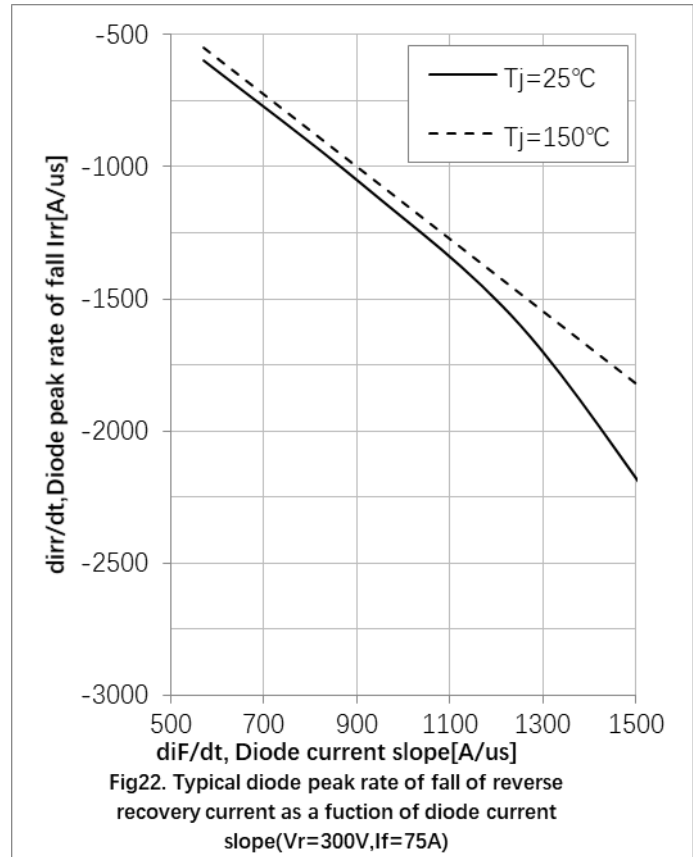
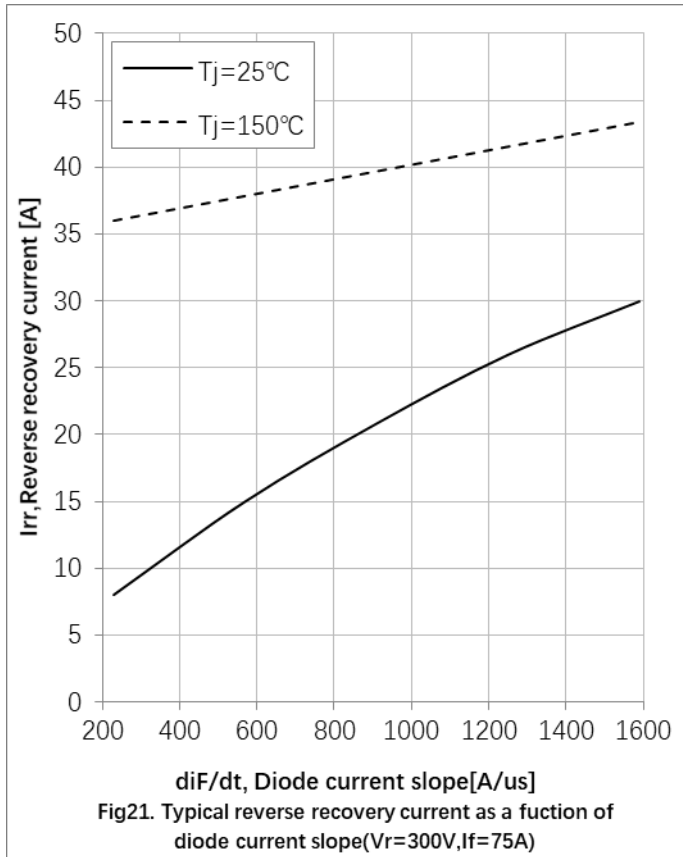
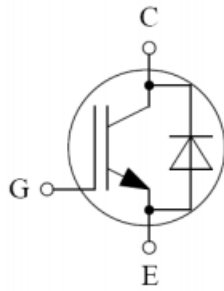


Fig16. Typical capacitance as a function of collector-emitter voltage

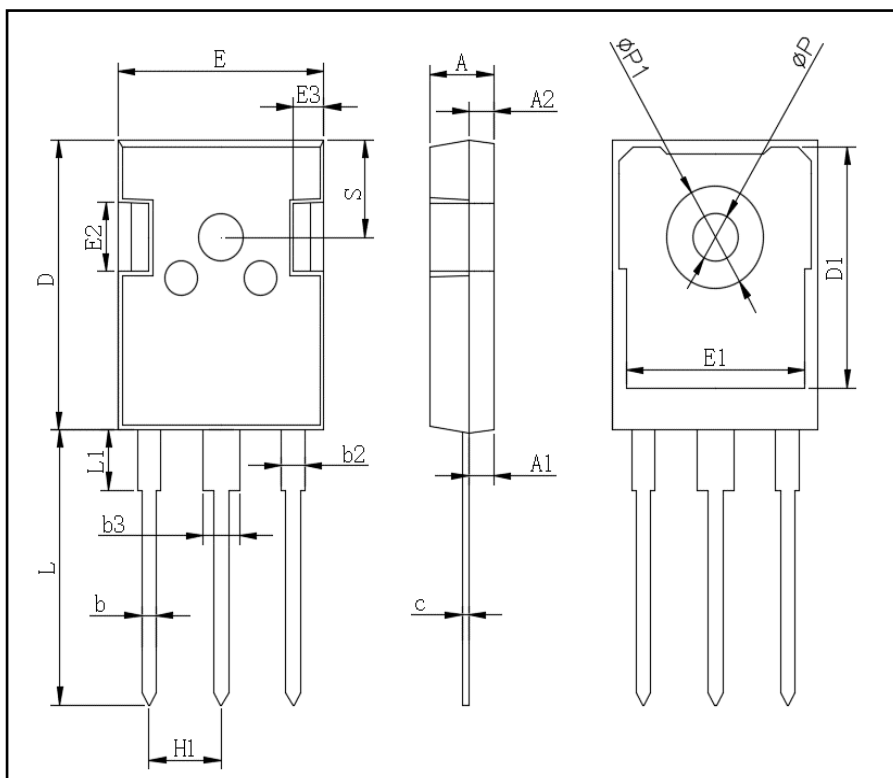




Circuit Diagram



Package Outline Information



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
ΦP	3.40	3.80
ΦP1	-	7.30
S	6.15TYP	
H1	5.44TYP	
b3	2.80	3.20